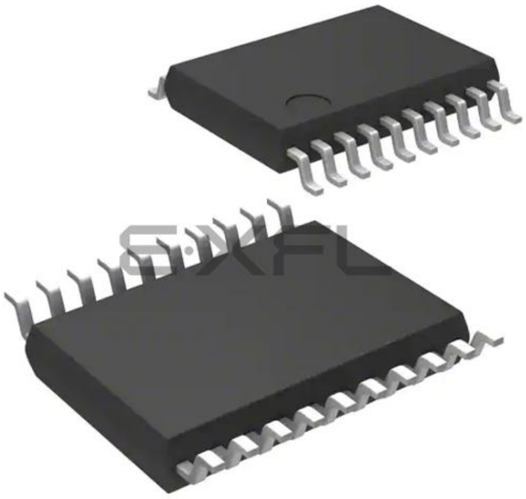

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	STM8A
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	640 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 7x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8af6223paau

4 Product overview

The following section intends to give an overview of the basic features of the products covered by this datasheet.

For more detailed information on each feature please refer to STM8S series and STM8AF series 8-bit microcontrollers reference manual (RM0016).

4.1 Central processing unit (CPU)

The 8-bit STM8 core is designed for code efficiency and performance.

It contains 6 internal registers which are directly addressable in each execution context, 20 addressing modes including indexed indirect and relative addressing and 80 instructions.

4.1.1 Architecture and registers

- Harvard architecture
- 3-stage pipeline
- 32-bit wide program memory bus - single cycle fetching for most instructions
- X and Y 16-bit index registers, enabling indexed addressing modes with or without offset and read-modify-write type data manipulations
- 8-bit accumulator
- 24-bit program counter - 16-Mbyte linear memory space
- 16-bit stack pointer - access to a 64 Kbyte level stack
- 8-bit condition code register - 7 condition flags for the result of the last instruction.

4.1.2 Addressing

- 20 addressing modes
- Indexed indirect addressing mode for look-up tables located anywhere in the address space
- Stack pointer relative addressing mode for local variables and parameter passing

4.1.3 Instruction set

- 80 instructions with 2-byte average instruction size
- Standard data movement and logic/arithmetic functions
- 8-bit by 8-bit multiplication
- 16-bit by 8-bit and 16-bit by 16-bit division
- Bit manipulation
- Data transfer between stack and accumulator (push/pop) with direct stack access
- Data transfer using the X and Y registers or direct memory-to-memory transfers

5 Pinout and pin description

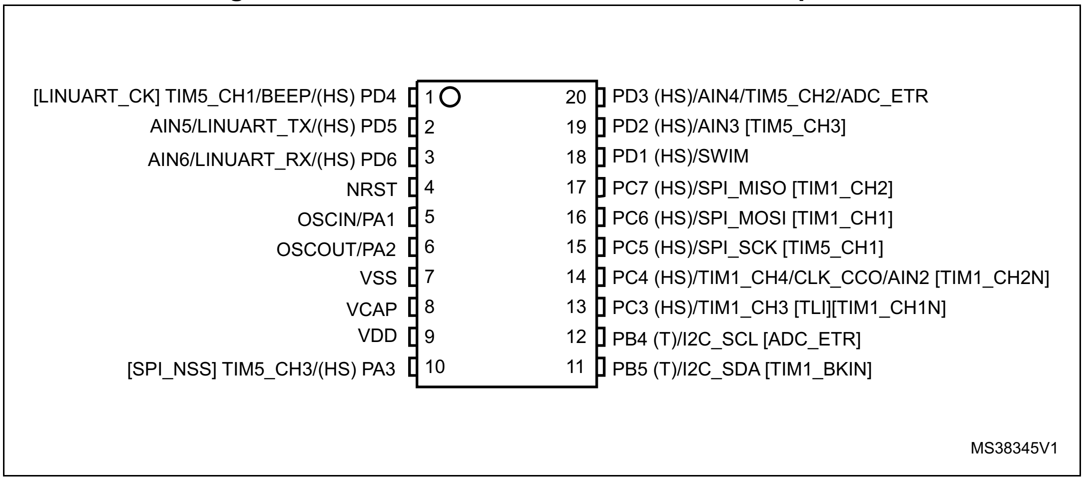
The following table presents the meaning of the abbreviations in use in the pin description tables in this section.

Table 5. Legend/abbreviations for pinout tables

Type	I= input, O = output, S = power supply	
Level	Input	CM = CMOS (standard for all I/Os)
	Output	HS = High sink
Output speed	O1 = Slow (up to 2 MHz) O2 = Fast (up to 10 MHz) O3 = Fast/slow programmability with slow as default state after reset O4 = Fast/slow programmability with fast as default state after reset	
Port and control configuration	Input	float = floating, wpu = weak pull-up
	Output	T = true open drain, OD = open drain, PP = push pull
Reset state	Bold X (pin state after internal reset release). Unless otherwise specified, the pin state is the same during the reset phase and after the internal reset release.	

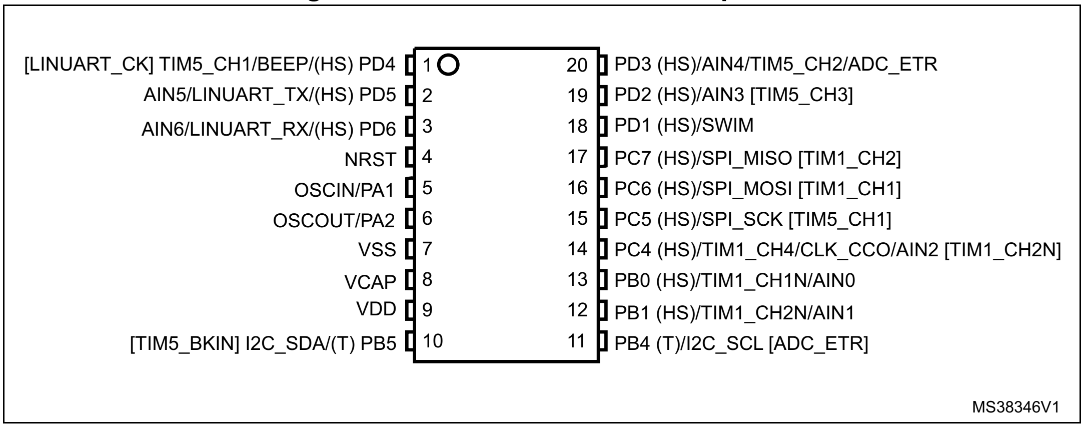
5.1 TSSOP20 pinouts and pin descriptions

Figure 3. STM8AF6213/STM8AF6223 TSSOP20 pinout



1. (HS) high sink capability.
2. (T) true open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).

Figure 4. STM8AF6223A TSSOP20 pinout



1. (HS) high sink capability.
2. (T) true open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).

Table 6. STM8AF6213/STM8AF6223 TSSOP20 pin description

TSSOP	Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
			floating	wpu	Ext. interrupt	High sink[(1)]	Speed	OD	PP			
1	PD4/ TIM5_CH1/ BEEP [LINUART_CK]	I/O	X	X	X	HS	O3	X	X	Port D4	Timer 5 - channel 1/BEEP output	LINUART clock [AFR2]
2	PD5/ AIN5/ LINUART_TX	I/O	X	X	X	HS	O3	X	X	Port D5	Analog input 5/ LINUART data transmit	-
3	PD6/ AIN6/ LINUART_RX	I/O	X	X	X	HS	O3	X	X	Port D6	Analog input 6/ LINUART data receive	-
4	NRST	I/O	-	X	-	-	-	-	-	Reset		
5	PA1/ OSCIN[(2)]	I/O	X	X	X	-	O1	X	X	Port A1	Resonator/ crystal in	-
6	PA2/ OSCOUT	I/O	X	X	X	O1	X	X		Port A2	Resonator/ crystal out	-
7	VSS	S	-	-	-	-	-	-	-	Digital ground		
8	VCAP	S	-	-	-	-	-	-	-	1.8 V regulator capacitor		
9	VDD	S	-	-	-	-	-	-	-	Digital power supply		

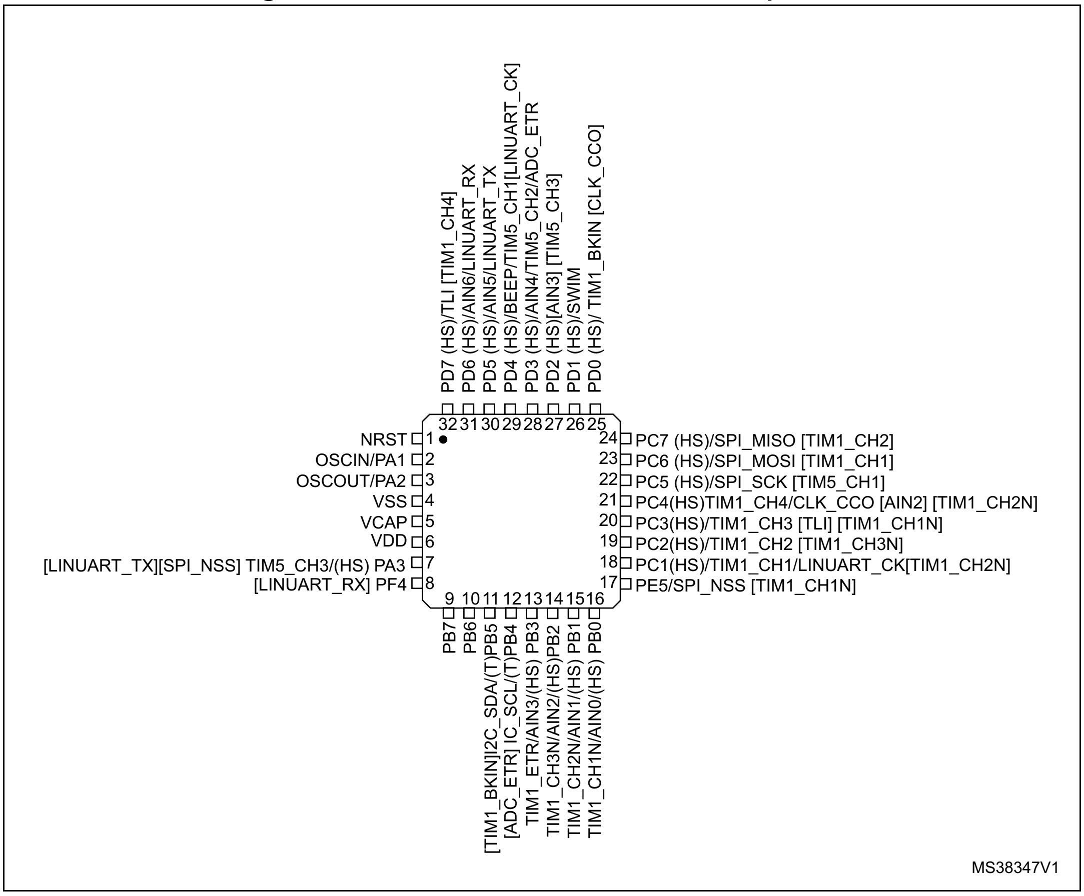
Table 7. STM8AF6223A TSSOP20 pin description (continued)

TSSOP	Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
			floating	wpu	Ext. interrupt	High sink(1)	Speed	OD	PP			
16	PC6/ SPI_MOSI [TIM1_CH1]	I/O	X	X	X	HS	O3	X	X	Port C6	PI master out/slave in	Timer 1 channel 1 [AFR0]
17	PC7/ SPI_MISO [TIM1_CH2]	I/O	X	X	X	HS	O3	X	X	Port C7	SPI master in/ slave out	Timer 1 channel 2[AFR0]
18	PD1/ SWIM(4)	I/O	X	X	X	HS	O4	X	X	Port D1	SWIM data interface	-
19	PD2/AIN3/ TLI[TIM5_CH3]	I/O	X	X	X	HS	O3	X	X	Port D2	-	Analog input 3 [AFR2] Timer 5 - channel 3 [AFR1]
20	PD3/ AIN4/ TIM5_CH2/ ADC_ETR	I/O	X	X	X	HS	O3	X	X	Port D3	Analog input 4 Timer 52 - channel 2/ADC external trigger	-

1. I/O pins used simultaneously for high current source/sink must be uniformly spaced around the package. In addition, the total driven current must respect the absolute maximum ratings (see *Section 9.2: Absolute maximum ratings*).
2. When the MCU is in Halt/Active-halt mode, PA1 is automatically configured in input weak pull-up and cannot be used for waking up the device. In this mode, the output state of PA1 is not driven. It is recommended to use PA1 only in input mode if Halt/Active-halt is used in the application.
3. In the open-drain output column, 'T' defines a true open-drain I/O (P-buffer, weak pull-up, and protection diode to VDD are not implemented).
4. The PD1 pin is in input pull-up during the reset phase and after internal reset release.

5.2 LQFP32/VFQPN32 pinout and pin description

Figure 5. STM8AF6226 LQFP32/VFQPN32 pinout



1. (HS) high sink capability.
2. (T) true open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).

Table 8. STM8AF6226 LQFP32/VFQPN32 pin description

LQFP32 VFQPN32	Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
			floating	wpu	Ext. interrupt	High sink(1)	Speed	OD	PP			
1	NRST	I/O	-	X	-	-	-	-	-	Reset		-
2	PA1/ OSCIN(2)	I/O	X	X	X	-	O1	X	X	Port A1	Resonator/ crystal in	-
3	PA2/ OSCOUT	I/O	X	X	X	-	O1	X	X	Port A2	Resonator/ crystal out	-

Table 8. STM8AF6226 LQFP32/VFQPN32 pin description (continued)

LQFP32 VFQPN32	Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
			floating	wpu	Ext. interrupt	High sink[(1)]	Speed	OD	PP			
17	PE5/ SPI_NSS [TIM1_CH1N]	I/O	**X**	X	X	HS	O3	X	X	Port E5	SPI master/ slave select	Timer 1 - inverted channel 1 [AFR1:0]
18	PC1/ TIM1_CH1/ LINUART_CK [TIM1_CH2N]	I/O	**X**	X	X	HS	O3	X	X	Port C1	Timer 1 - channel 1 LINUART clock	Timer 1 - inverted channel 2 [AFR1:0]
19	PC2/ TIM1_CH2 [TIM1_CH3N]	I/O	**X**	X	X	HS	O3	X	X	Port C2	Timer 1 - channel 2	Timer 1 - inverted channel 3 [AFR1:0]
20	PC3/ TIM1_CH3/[TLI] [TIM1_CH1N]	I/O	**X**	X	X	HS	O3	X	X	Port C3	Timer 1 - channel 3	Top level interrupt [AFR3] Timer 1 inverted channel 1 [AFR7]
21	PC4/ TIM1_CH4/ CLK_CCO/[AIN 2][TIM1_CH2N]	I/O	**X**	X	X	HS	O3	X	X	Port C4	Timer 1 - channel 4 /configurable clock output	Analog input 2 [AFR2]Timer 1 inverted channel 2 [AFR7]
22	PC5/SPI_SCK [TIM5_CH1]	I/O	**X**	X	X	HS	O3	X	X	Port C5	SPI clock	Timer 5 channel 1 [AFR0]
23	PC6/ SPI_MOSI [TIM1_CH1]	I/O	**X**	X	X	HS	O3	X	X	Port C6	PI master out/slave in	Timer 1 channel 1 [AFR0]
24	PC7/ SPI_MISO [TIM1_CH2]	I/O	**X**	X	X	HS	O3	X	X	Port C7	SPI master in/ slave out	Timer 1 channel 2[AFR0]
25	PD0/ TIM1_BKIN [CLK_CCO]	I/O	**X**	X	X	HS	O3	X	X	Port D0	Timer 1 - break input	Configurable clock output [AFR5]
26	PD1/ SWIM[(4)]	I/O	X	**X**	X	HS	O4	X	X	Port D1	SWIM data interface	-

6 Memory and register map

6.1 Memory map

Figure 6. Memory map

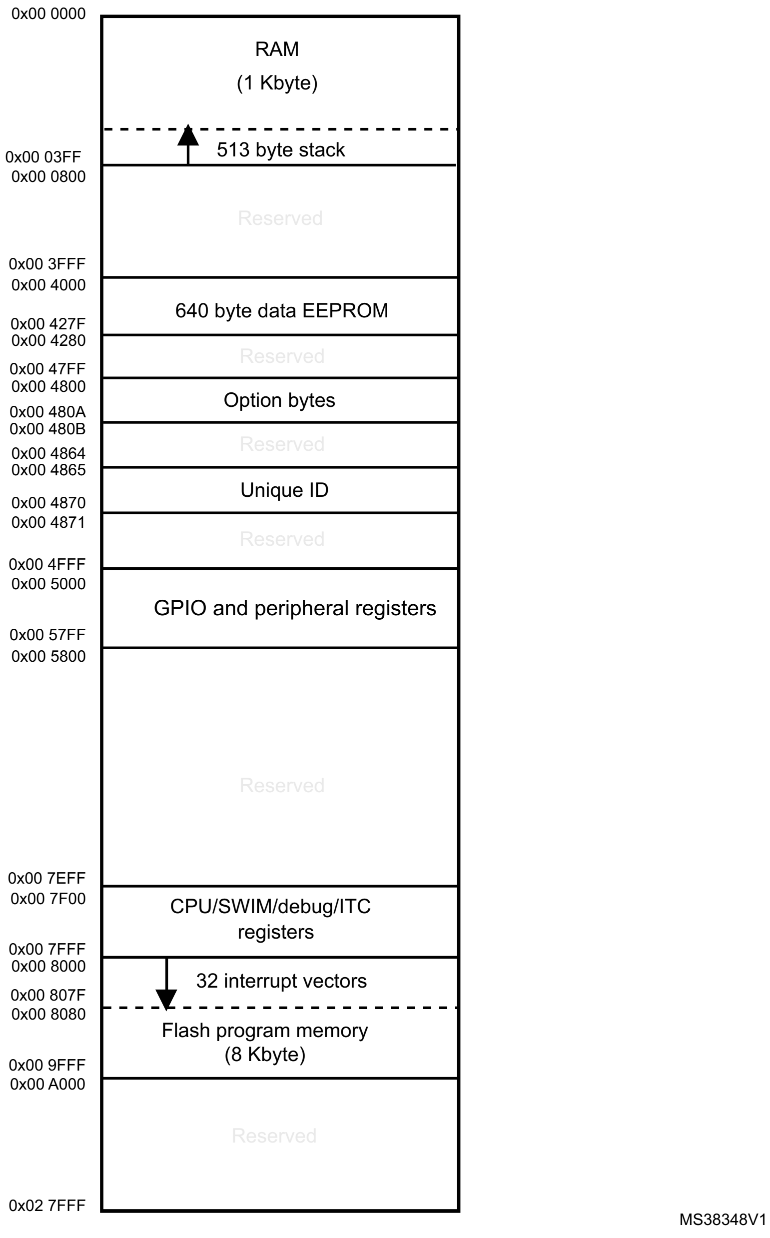


Table 10. I/O port hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5014	Port E	PE_ODR	Port E data output latch register	0x00
0x00 5015		PE_IDR	Port E input pin value register	0xXX(1)
0x00 5016		PE_DDR	Port E data direction register	0x00
0x00 5017		PE_CR1	Port E control register 1	0x00
0x00 5018		PE_CR2	Port E control register 2	0x00
0x00 5019	Port F	PF_ODR	Port F data output latch register	0x00
0x00 501A		PF_IDR	Port F input pin value register	0xXX(1)
0x00 501B		PF_DDR	Port F data direction register	0x00
0x00 501C		PF_CR1	Port F control register 1	0x00
0x00 501D		PF_CR2	Port F control register 2	0x00

1. Depends on the external circuitry.

Table 11. General hardware register map

Address	Block	Register label	Register name	Reset status
0x00 501E to 0x00 5069	Reserved area (60 byte)			
0x00 505A	Flash	FLASH_CR1	Flash control register 1	0x00
0x00 505B		FLASH_CR2	Flash control register 2	0x00
0x00 505C		FLASH_NCR2	Flash complementary control register 2	0xFF
0x00 505D		FLASH_FPR	Flash protection register	0x00
0x00 505E		FLASH_NFPR	Flash complementary protection register	0xFF
0x00 505F		FLASH_IAPSR	Flash in-application programming status register	0x40
0x00 5060 to 0x00 5061	Reserved area (2 byte)			
0x00 5062	Flash	FLASH_PUKR	Flash Program memory unprotection register	0x00
0x00 5063	Reserved area (1 byte)			
0x00 5064	Flash	FLASH_DUKR	Data EEPROM unprotection register	0x00
0x00 5065 to 0x00 509F	Reserved area (59 byte)			
0x00 50A0	ITC	EXTI_CR1	External interrupt control register 1	0x00
0x00 50A1		EXTI_CR2	External interrupt control register 2	0x00
0x00 50A2 to 0x00 50B2	Reserved area (17 byte)			

Table 11. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 50B3	RST	RST_SR	Reset status register	0xXX(1)
0x00 50B4 to 0x00 50BF	Reserved area (12 byte)			
0x00 50C0	CLK	CLK_ICKR	Internal clock control register	0x01
0x00 50C1		CLK_ECKR	External clock control register	0x00
0x00 50C2	Reserved area (1 byte)			
0x00 50C3	CLK	CLK_CMSR	Clock master status register	0xE1
0x00 50C4		CLK_SWR	Clock master switch register	0xE1
0x00 50C5		CLK_SWCR	Clock switch control register	0xXX
0x00 50C6		CLK_CKDIVR	Clock divider register	0x18
0x00 50C7		CLK_PCKENR1	Peripheral clock gating register 1	0xFF
0x00 50C8		CLK_CSSR	Clock security system register	0x00
0x00 50C9		CLK_CCOR	Configurable clock control register	0x00
0x00 50CA		CLK_PCKENR2	Peripheral clock gating register 2	0xFF
0x00 50CB	Reserved area (1 byte)			
0x00 50CC	CLK	CLK_HSITRIMR	HSI clock calibration trimming register	0x00
0x00 50CD		CLK_SWIMCCR	SWIM clock control register	0bXXXX XXX0
0x00 50CE to 0x00 50D0	Reserved area (3 byte)			
0x00 50D1	WWDG	WWDG_CR	WWDG control register	0x7F
0x00 50D2		WWDG_WR	WWDR window register	0x7F
0x00 50D3 to 0x00 50DF	Reserved area (13 byte)			
0x00 50E0	IWDG	IWDG_KR	IWDG key register	0xXX(2)
0x00 50E1		IWDG_PR	IWDG prescaler register	0x00
0x00 50E2		IWDG_RLR	IWDG reload register	0xFF
0x00 50E3 to 0x00 50EF	Reserved area (13 byte)			
0x00 50F0	AWU	AWU_CSR1	AWU control/status register 1	0x00
0x00 50F1		AWU_APR	AWU asynchronous prescaler buffer register	0x3F
0x00 50F2		AWU_TBR	AWU timebase selection register	0x00
0x00 50F3	BEEP	BEEP_CSR	BEEP control/status register	0x1F
0x00 50F4 to 0x00 50FF	Reserved area (12 byte)			

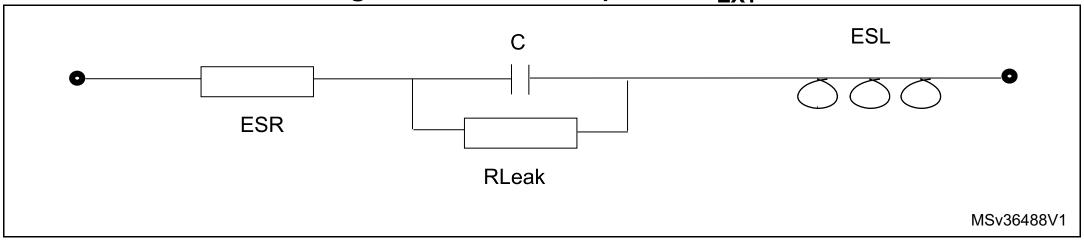
Table 11. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 5300	TIM5	TIM5_CR1	TIM5 control register 1	0x00
0x00 5301		TIM5_CR2	TIM5 control register 2	0x00
0x00 5302		TIM5_SMCR	TIM5 slave mode control register	0x00
0x00 5303		TIM5_IER	TIM5 interrupt enable register	0x00
0x00 5304		TIM5_SR1	TIM5 status register 1	0x00
0x00 5305		TIM5_SR2	TIM5 status register 2	0x00
0x00 5306		TIM5_EGR	TIM5 event generation register	0x00
0x00 5307		TIM5_CCMR1	TIM5 capture/compare mode register 1	0x00
0x00 5308		TIM5_CCMR2	TIM5 capture/compare mode register 2	0x00
0x00 5309		TIM5_CCMR3	TIM5 capture/compare mode register 3	0x00
0x00 530A		TIM5_CCER1	TIM5 capture/compare enable register 1	0x00
0x00 530B		TIM5_CCER2	TIM5 capture/compare enable register 2	0x00
00 530C0x		TIM5_CNTRH	TIM5 counter high	0x00
0x00 530D		TIM5_CNTRL	TIM5 counter low	0x00
0x00 530E		TIM5_PSCR	TIM5 prescaler register	0x00
0x00 530F		TIM5_ARRH	TIM5 auto-reload register high	0xFF
0x00 5310		TIM5_ARRL	TIM5 auto-reload register low	0xFF
0x00 5311		TIM5_CCR1H	TIM5 capture/compare register 1 high	0x00
0x00 5312		TIM5_CCR1L	TIM5 capture/compare register 1 low	0x00
0x00 5313		TIM5_CCR2H	TIM5 capture/compare reg. 2 high	0x00
0x00 5314		TIM5_CCR2L	TIM5 capture/compare register 2 low	0x00
0x00 5315		TIM5_CCR3H	TIM5 capture/compare register 3 high	0x00
0x00 5316		TIM5_CCR3L	TIM5 capture/compare register 3 low	0x00
0x00 5317 to 0x00 533F	Reserved area (43 byte)			
0x00 5340	TIM6	TIM6_CR1	TIM6 control register 1	0x00
0x00 5341		TIM6_CR2	TIM6 control register 2	0x00
0x00 5342		TIM6_SMCR	TIM6 slave mode control register	0x00
0x00 5343		TIM6_IER	TIM6 interrupt enable register	0x00
0x00 5344		TIM6_SR	TIM6 status register	0x00
0x00 5345		TIM6_EGR	TIM6 event generation register	0x00
0x00 5346		TIM6_CNTR	TIM6 counter	0x00
0x00 5347		TIM6_PSCR	TIM6 prescaler register	0x00
0x00 5348		TIM6_ARR	TIM6 auto-reload register	0xFF

9.3.1 VCAP external capacitor

Stabilization for the main regulator is achieved connecting an external capacitor C_{EXT} to the V_{CAP} pin. C_{EXT} is specified in *Table 26*. Care should be taken to limit the series inductance to less than 15 nH.

Figure 10. External capacitor C_{EXT}



1. Legend: ESR is the equivalent series resistance and ESL is the equivalent inductance.

9.3.2 Supply current characteristics

The current consumption is measured as described in *Section 4.3: Interrupt controller*.

Total current consumption in run mode

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled (clock stopped by peripheral clock gating registers) except if explicitly mentioned.

Subject to general operating conditions for V_{DD} and T_A.

Unless otherwise specified, data are based on characterization results, and not tested in production.

Table 28. Total current consumption with code execution in run mode at V_{DD} = 5 V

Symbol	Parameter	Conditions		Typ	Max	Unit
$I_{DD(RUN)}$	Supply current in run mode, code executed from RAM	$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	2.3	-	mA
			HSE user ext. clock (16 MHz)	2	2.35	
			HSI RC osc. (16 MHz)	1.7	2(1)	
		$f_{CPU} = f_{MASTER}$/128= 125 kHz	HSE user ext. clock (16 MHz)	0.86	-	
			HSI RC osc. (16 MHz)	0.7	0.87	
		$f_{CPU} = f_{MASTER}$/128= 15.625 kHz	HSI RC osc. (16 MHz/8)	0.46	0.58	
		$f_{CPU} = f_{MASTER}$ = 28 kHz	LSI RC osc. (128 kHz)	0.41	0.55	

Total current consumption and timing in forced reset state

Table 37. Total current consumption and timing in forced reset state

Symbol	Parameter	Conditions	Typ	Max[1]	Unit
$I_{DD(R)}$	Supply current in reset state[2]	V_{DD}= 5 V	400	-	µA
		V_{DD}= 3.3 V	300	-	
$t_{RESETBL}$	Reset pin release to vector fetch	-	-	150	µs

1. Guaranteed by design.
2. Characterized with all I/Os tied to V_{SS}.

Current consumption for on-chip peripherals

Subject to general operating conditions for V_{DD} and T_A.

HSI internal RC/f_{CPU} = f_{MASTER} = 16 MHz, V_{DD} = 5 V

Table 38. Peripheral current consumption

Symbol	Parameter	Typ	Unit
$I_{DD(TIM1)}$	TIM1 supply current[1]	210	µA
$I_{DD(TIM5)}$	TIM5 supply current[1]	130	
$I_{DD(TIM6)}$	TIM6 supply current[1]	50	
$I_{DD(UART1)}$	LINUART supply current[2]	120	
$I_{DD(SPI)}$	SPI supply current[2]	45	
$I_{DD(I2C)}$	I2C supply current[2]	65	
$I_{DD(ADC1)}$	ADC1 supply current[3]	1000	

1. Data based on a differential I_{DD} measurement between reset configuration and timer counter running at 16 MHz. No IC/OC programmed (no I/O pads toggling). Not tested in production.
2. Data based on a differential I_{DD} measurement between the on-chip peripheral when kept under reset and not clocked and the on-chip peripheral when clocked and not kept under reset. No I/O pads toggling. Not tested in production.
3. Data based on a differential I_{DD} measurement between reset configuration and continuous A/D conversions. Not tested in production.

Figure 15. Typ $I_{DD(WFI)}$ vs. f_{CPU} HSE user external clock, V_{DD} = 5 V

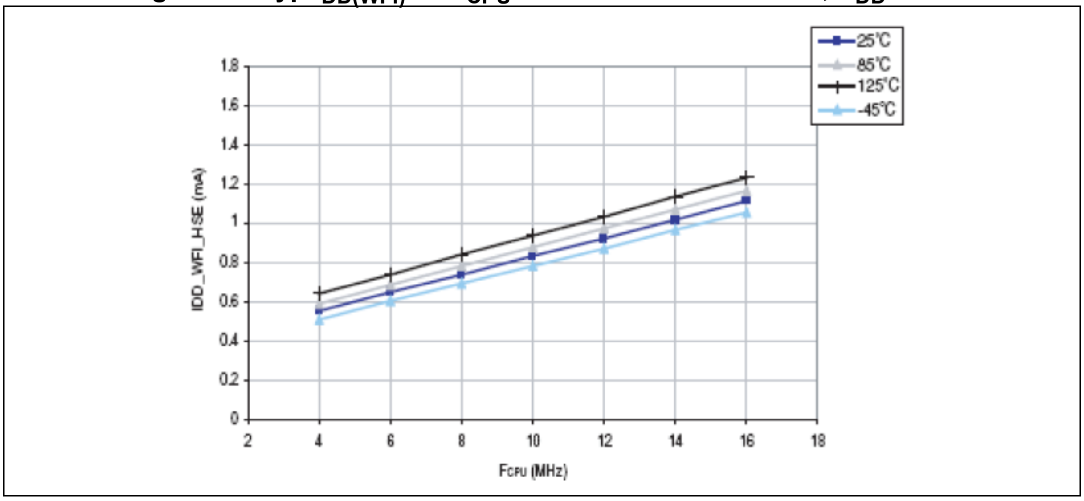


Figure 16. Typ $I_{DD(WFI)}$ vs. V_{DD} HSI RC osc., f_{CPU} = 16 MHz

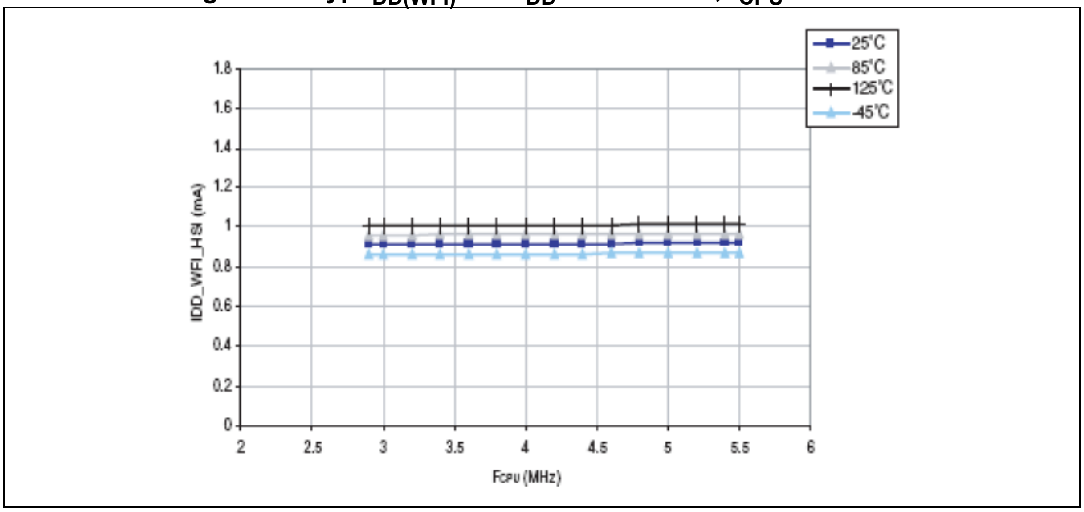


Figure 33. Typical NRST pull-up resistance vs V_{DD} @ 4 temperatures

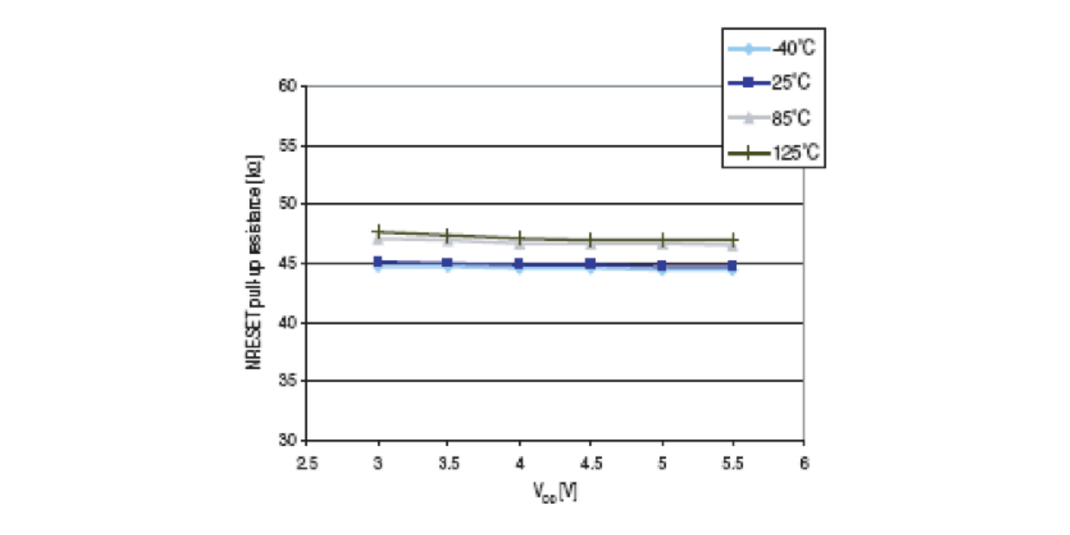
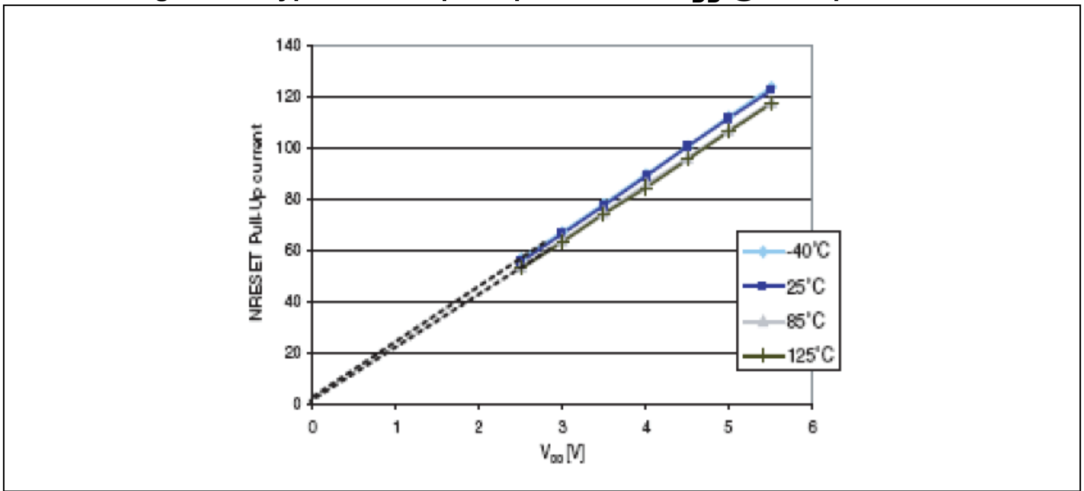


Figure 34. Typical NRST pull-up current vs V_{DD} @ 4 temperatures



The reset network shown in *Figure 35* protects the device against parasitic resets. The user must ensure that the level on the NRST pin can go below $V_{IL(NRST)}$ max (see *Table 51: NRST pin characteristics*), otherwise the reset is not taken into account internally.

For power consumption sensitive applications, the external reset capacitor value can be reduced to limit the charge/discharge current. If NRST signal is used to reset external circuitry, attention must be taken to the charge/discharge time of the external capacitor to fulfill the external devices reset timing conditions. Minimum recommended capacity is 100 nF.

Table 55. ADC accuracy with RAIN < 10 kΩ, V_{DD} = 5 V

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$\|E_T\|$	Total unadjusted error(2)	f_{ADC} = 2 MHz	1.6	3.5	LSB
		f_{ADC} = 4 MHz	2.2	4	
		f_{ADC} = 6 MHz	2.4	4.5	
$\|E_O\|$	Offset error(2)	f_{ADC} = 2 MHz	1.1	2.5	
		f_{ADC} = 4 MHz	1.5	3	
		f_{ADC} = 6 MHz	1.8	3	
$\|E_G\|$	Gain error(2)	f_{ADC} = 2 MHz	1.5	3	
		f_{ADC} = 4 MHz	2.1	3	
		f_{ADC} = 6 MHz	2.2	4	
$\|E_D\|$	Differential linearity error(2)	f_{ADC} = 2 MHz	0.7	1.5	
		f_{ADC} = 4 MHz	0.7	1.5	
		f_{ADC} = 6 MHz	0.7	1.5	
$\|E_L\|$	Integral linearity error(2)	f_{ADC} = 2 MHz	0.6	1.5	
		f_{ADC} = 4 MHz	0.8	2	
		f_{ADC} = 6 MHz	0.8	2	

1. Max value is based on characterization, not tested in production.
2. ADC accuracy vs. negative injection current: Injecting negative current on any of the analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in the I/O port pin characteristics section does not affect the ADC accuracy.

Table 56. ADC accuracy with RAIN < 10 kΩ, V_{DD} = 3.3 V

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$\|E_T\|$	Total unadjusted error	f_{ADC} = 2 MHz	1.6	3.5	LSB
		f_{ADC} = 4 MHz	1.9	4	
$\|E_O\|$	Offset error	f_{ADC} = 2 MHz	1	2.5	
		f_{ADC} = 4 MHz	1.5	2.5	
$\|E_G\|$	Gain error	f_{ADC} = 2 MHz	1.3	3	
		f_{ADC} = 4 MHz	2	3	
$\|E_D\|$	Differential linearity error	f_{ADC} = 2 MHz	0.7	1	
		f_{ADC} = 4 MHz	0.7	1.5	
$\|E_L\|$	Integral linearity error	f_{ADC} = 2 MHz	0.6	1.5	
		f_{ADC} = 4 MHz	0.8	2	

1. Max value is based on characterization, not tested in production.

9.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

While executing a simple application (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **FESD**: Functional electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be recovered by applying a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see the application note reference AN1015).

Table 57. EMS data

Symbol	Parameter	Conditions	Level/class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A= 25 °C, f_{MASTER} = 16 MHz (HSI clock), Conforms to IEC 61000-4-2	2/B(1)
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}= 3.3 V, T_A= 25 °C, f_{MASTER} = 16 MHz (HSI clock), Conforms to IEC 61000-4-4	4/A

1. Data obtained with HSI clock configuration, after applying hardware recommendations described in AN2860 (EMC guidelines for STM8S microcontrollers).

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC 61967-2 which specifies the board and the loading of each pin.

Table 58. EMI data

Symbol	Parameter	Conditions				Unit
		General conditions	Monitored frequency band	Max f_{HSE}/f_{CPU}(1)		
				16 MHz/ 8 MHz	16 MHz/ 16 MHz	
S_{EMI}	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP32 package conforming to IEC 61967-2	0.1 MHz to 30 MHz	5	5	dBµV
			30 MHz to 130 MHz	4	5	
			130 MHz to 1 GHz	5	5	
	EMI level		—	2.5	2.5	level

1. Guaranteed by characterization results.

Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, DLU and LU) using specific measurement methods, the product is stressed to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (one positive then one negative pulses separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). One model can be simulated: Human body model. This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 59. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human body model)	T_A = 25°C, conforming to JESD22-A114	3A	4000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charge device model)	T_A= 25°C, conforming to JESD22-C101	3	500	
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine model)	T_A= 25°C, conforming to JESD22-A115	B	200	

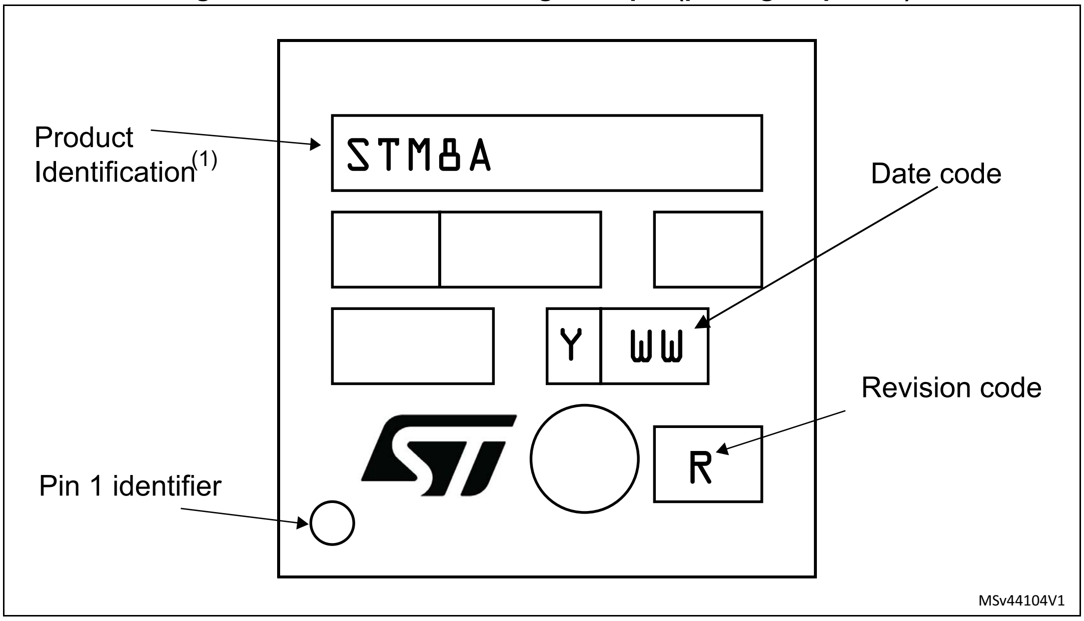
1. Guaranteed by characterization results.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 50. VFQFPN32 marking example (package top view)



1. Parts marked as “ES” or “E” are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST’s Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

10.4 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 26: General operating conditions*.

T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

– T_{Amax} is the maximum ambient temperature in °C

– Θ_{JA} is the package junction-to-ambient thermal resistance in ° C/W

– P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$)

– P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

– $P_{I/Omax}$ represents the maximum power dissipation on output pins
Where:
$P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
taking into account the actual V_{OL}/I_{OL} and V_{OH}/I_{OH} of the I/Os at low and high level in the application.

Table 64. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient TSSOP20 - 4 x 4 mm	110	°C/W
	Thermal resistance junction-ambient LQFP 32 - 7 x 7 mm	60	
	Thermal resistance junction-ambient VFQFPN32 - 5 x 5 mm	TBD	

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

10.4.1 Reference document

JESD51-2 integrated circuits thermal test method environment conditions - natural convection (still air). Available from www.jedec.org.

10.4.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the order code (see *Section 11: Ordering information*).

The following example shows how to calculate the temperature range needed for a given application.